

# [METHOD OF FABRICATING A STRINGERLESS FLASH MEMORY]

## Abstract of Disclosure

A stringer block is formed on the interface between a HDP silicon oxide layer and a silicon substrate. During an etching process for defining the profile of a floating gate, the stringer block functions to expose a bottom corner stringer. Following that, a polysilicon etching process effectively removes the bottom corner stringer. As a result, a stringerless flash memory cell is formed to prevent leakage currents, resulting from the bottom corner stringer, and improve both the reliability and data retention ability of the device.

## Figures

[illegible]